

1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



Product data sheet

1. General description

Planar passivated sensitive gate four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in general purpose bidirectional switching and phase control applications. This sensitive gate "series E" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct triggering from low power drivers and logic ICs
- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate
- Triggering in all four quadrants

3. Applications

- General purpose motor control
- General purpose switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	-	95	А
Tj	junction temperature		-	-	125	°C
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 \text{ °C}$; Fig. 1; Fig. 2; Fig. 3	-	-	12	А
Static charac	teristics		'	'		
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	2.5	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$	-	4	10	mA





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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	11	25	mA
Dynamic char	acteristics					,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	7 7	sym051
3	G	gate		J
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT138-800E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BT138-800E/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	12	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	95	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	-	105	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	45	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/µs; T2+ G+	-	50	A/µs
		$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s};$ T2+ G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G-	-	50	A/µs
		I_T = 20 A; I_G = 0.2 A; dI_G/dt = 0.2 A/ μ s; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	2	Α
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

Product data sheet

3 / 13

4Q Triac

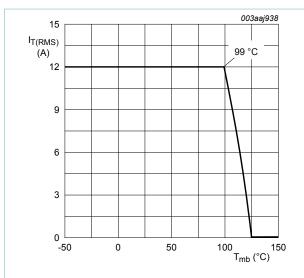


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

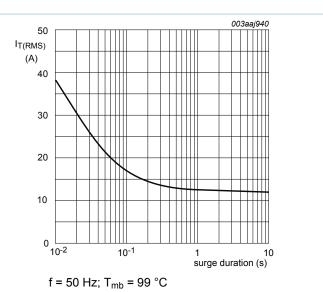
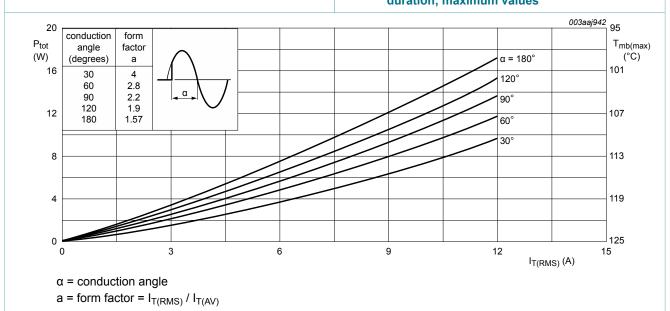


Fig. 2. RMS on-state current as a function of surge duration; maximum values



Total power dissipation as a function of RMS on-state current; maximum values Fig. 3.

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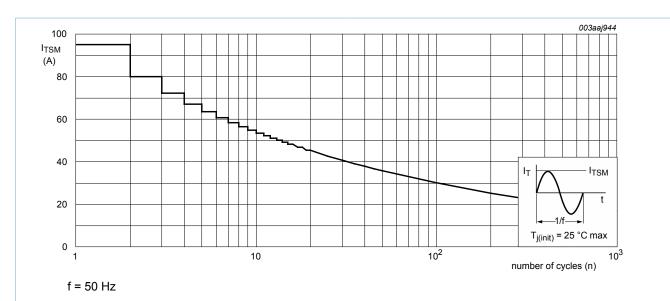
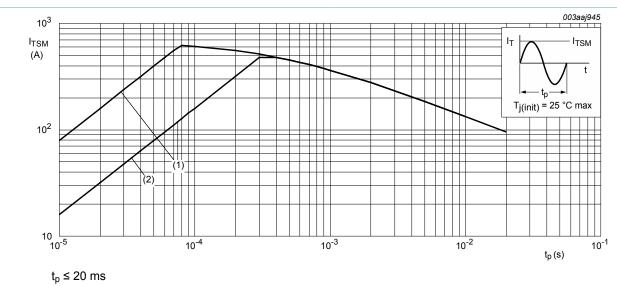


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



(1) dI_T/dt limit

(2) T2- G+ quadrant limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
from junction	thermal resistance	full cycle; Fig. 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W

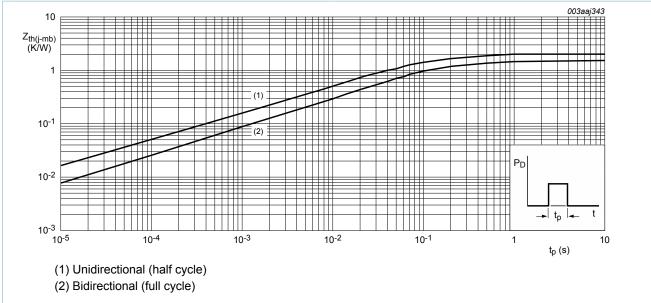


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

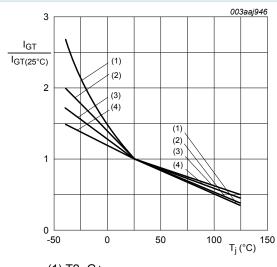
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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'		'	
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 7</u>	-	2.5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 7}}$	-	4	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 7</u>	-	5	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$	-	11	25	mA
L	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 8</u>	-	-	30	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 8</u>	-	-	40	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	40	mA
Н	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	30	mA
/ _T	on-state voltage	I _T = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.4	1.65	V
/ _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 11	0.25	0.4	-	V
D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		1	1	1	
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	-	150	-	V/µs
tgt	gate-controlled turn-on time	I_{TM} = 16 A; V_D = 800 V; I_G = 0.1 A; $dI_G/$ dt = 5 A/ μ s	-	2	-	μs

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- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

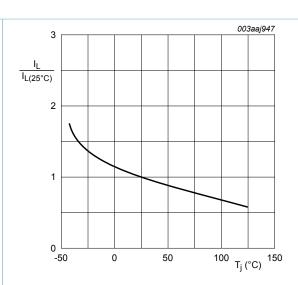
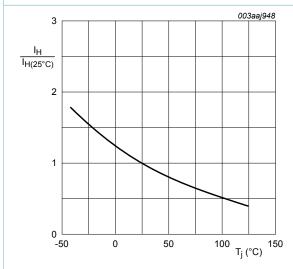
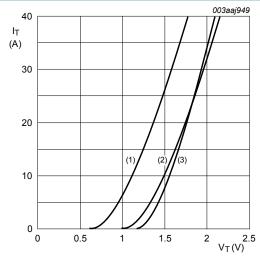


Fig. 8. Normalized latching current as a function of junction temperature



Normalized holding current as a function of junction temperature



 $V_o = 1.175 \text{ V}; R_s = 0.0316 \Omega$

- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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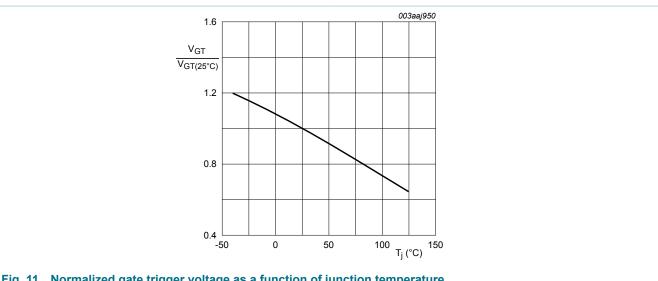


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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10. Package outline

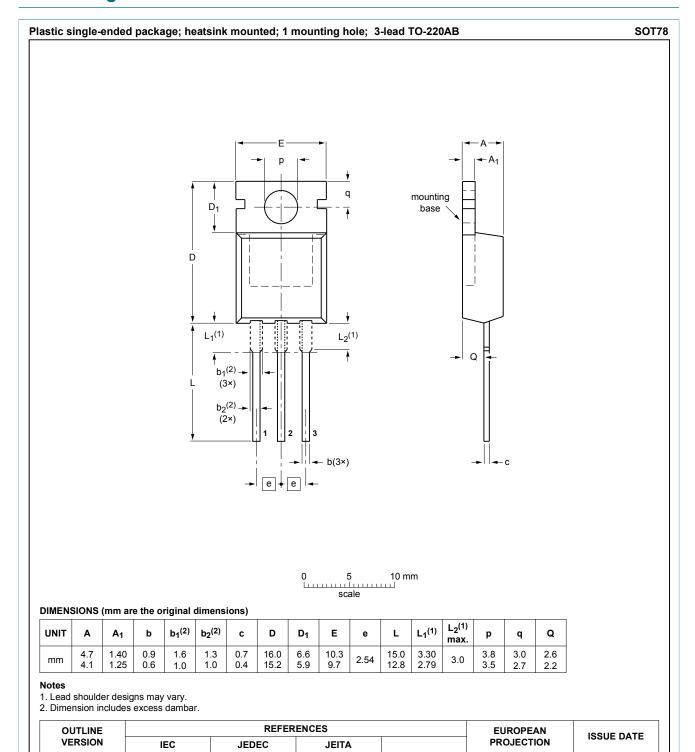


Fig. 12. Package outline TO-220AB (SOT78)

3-lead TO-220AB

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BT138-800E

SOT78

SC-46

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	3
8	Thermal characteristics	6
9	Characteristics	7
10	Package outline	10
11	Legal information	
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	
11.4	Trademarks	12

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13 / 13

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